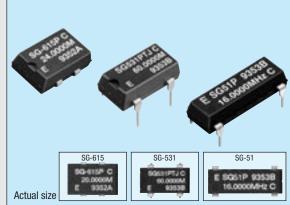
# soj high-frequency crystal oscillator SG-615 / 531 / 51 series

Product number (please refer to page 2)

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### Q32510xxxxxxx00

- High-density mounting-type SMD.
- Cylindrical AT crystal unit builtin, thus assuring high reliability.
- Low current consumption by output enable function (OE) or standby function  $\overline{(ST)}.$
- Pin compatible with full-size metal can. (SG-51 series)
- Pin compatible with half-size metal can. (SG-531 series)
  Available for lead (Pb)-free soldering.
  Available for lead (Pb)-free terminal.



Recommended soldering pattern (Unit: mm)

### Specifications (characteristics)

Item		Symbol	Specifications			Remarks	
		Symbol	SG-615P SG-531P SG-51P	SG-615PTJ SG-531PTJ SG-51PTJ	SG-615PH SG-531PH SG-51PH	nemarks	
Output frequency range		fo	1.0250 MHz to 26.0000 MHz 26.0001 MHz to 66.6667 MHz		Refer to Operating condition and Frequency range		
Power source	Max. supply voltage	VDD-GND	-0.3 V to +7.0 V -0.5 V to +7.0 V		-0.5 V to +7.0 V		
voltage	Operating voltage	Vdd	5.0 V±0.5 V				
Temperature	Storage temperature	Tstg	-55 °C to +125 °C		Stored as bare product after unpacking		
range	Operating temperature	TOPR	-20 °C to +70 °C (-40 °C to +85 °C)		Refer to Operating condition and Frequency range		
Frequency stability		$\Delta f/f_0$	B: ±50 x 10 <sup>-6</sup> C: ±100 x 10 <sup>-6</sup>		Refer to Operating condition and Frequency range		
Current consumption	1	lop	23 mA Max.	35 mA Max.		No load condition	
Output disable curre	nt	loe	12 mA Max.	28 mA Max.	20 mA Max.	OE = GND	
Duty		tw/ t	40 % to 60 %	-	40 % to 60 %	CMOS load: 1/2 VDD	
Duty		lw/ l	45 % to 55 % –		TTL load: 1.4 V		
Output voltage		Vон	Vdd -0.4 V Min.	2.4 V Min.	Vdd -0.4 V Min.	Іон = -400 µА (Р,РТЈ) / -4 mA (РН)	
Output voltage		Vol		0.4 V Max.		$I_{0L} = 16 \text{ mA} (P) / 8 \text{ mA} (PTJ) / 4 \text{ mA} (PH)$	
Output load condition (fan out)		CL	50 pF Max.	-	50 pF Max.		
Output Ioau conunto	ii (iaii oui)	Ν	10 TTL Max.	5 TTL Max.	-	C∟ ≤ 15 pF	
Output enable / disa	blo input voltago	Vih	2.0 V Min.	3.5 V Min.	2.0 V Min.	$I_{IH} = 1 \ \mu A Max. (OE = V_{DD})$	
Output enable / uisa	bie iliput voltage	VIL	0.8 V Max.	1.5 V Max.	0.8 V Max.	$IIL = -100 \ \mu A \ Min. (OE = GND)$ , PTJ : $IIL = -500 \ \mu A \ Min. (OE = GND)$	
Output rise time		tR	8 ns Max.	-	7 ns Max.	CMOS load: 20 % $\rightarrow$ 80 % VDD	
Output lise time		LK	o lis ividx.	5 ns Max.	-	TTL load: $0.4 V \rightarrow 2.4 V$	
Output fall time		tF	8 ns Max.	-	7 ns Max.	CMOS load: 80 % $\rightarrow$ 20 % VDD	
		L.	o ns wax.	5 ns Max.	-	TTL load: $2.4 \text{ V} \rightarrow 0.4 \text{ V}$	
Oscillation start up t	ime	tosc	4 ms Max.	4 ms Max. 10 ms Max.		Time at 4.5 V to be 0 s	
Aging		fa		±5 x 10 <sup>-6</sup> / year Max.		Ta = +25 °C, VDD = 5 V, first year	
Shock resistance		S.R.		±20 x 10 <sup>-6</sup> Max.		Three drops on a hard board from 750 mm or excitation test with 29400 m/s <sup>2</sup> x 0.3 ms x 1/2sine wave in 3 directions	

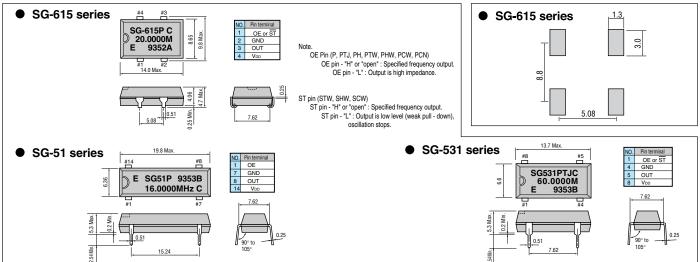
Note: • Unless otherwise stated, characteristics (specifications) shown in the above table are based on the rated operating temperature and voltage condition. • External by-pass capacitor is recommended.

### Operating condition and frequency range

Operating Voltage	Frequency stability(Operating temperature)	1 MHz	50 MHz	100 MHz		150 MHz
5 V±0.5 V	B: ±50 x 10 <sup>-6</sup> ( -20 °C to +70 °C)	1.025 SG-615/531/51P	26 55 SG-615/531/51PTJ/PH	SG-615/531PTW/STW/PHW/SHW	135	
	C: ±100 x 10 <sup>-6</sup> ( -20 °C to +70 °C)	1.025 SG-615/531/51P	26 66.6667 SG-615/531/51PTJ/PH	SG-615/531PTW/STW/PHW/SHW	135	
3.3 V±0.3 V	B: ±50 x 10 <sup>-6</sup> C: ±100 x 10 <sup>-6</sup> ( -20 °C to +70 °C)	1.5	26 66.6667	SG-615/531PCW/SCW	135	
	M: ±100 x 10 <sup>-6</sup> ( -40 °C to +85 °C)		SG-615PCN			

(Unit: mm)

### External dimensions



### Specifications (characteristics)

Item			Specifications				
		Symbol	SG-615PCG SG-531PCG	SG-615SCG SG-531SCG	SG-615PCN	Remarks	
Nominal frequency range		fo	1.5000 MHz to 26.0000 MHz		26.0001 MHz to 66.6667 MHz	Refer to Operating condition and Frequency rang	
Power source	Max. supply voltage	Vdd-GND	-0.5 V to +7.0 V				
voltage	Operating voltage	Vdd	2.7 V t	o 3.6 V	3.0 V to 3.6 V		
Temperature	Storage temperature	Tstg		-55 °C to +125 °C		Stored as bare product after unpacking	
range	Operating temperature	TOPR		-40 °C to +85 °C		Refer to Operating condition and Frequency range	
Frequency stability	Frequency stability		B : ±50 x 10 <sup>-6</sup> C : ±100 x 10 <sup>-6</sup>		D-6	-20 °C to +70 °C	
Frequency stability		$\Delta f/f_0$	M : ±100 x 10 <sup>-6</sup>			-40 °C to +85 °C	
Current consumption	n	ЮР	12 mA Max.		30 mA Max.	No load condition	
Output disable curre	ent	loe	10 mA Max.	-	15 mA Max.	OE = GND (PCG / PCN)	
Standby current		Ist	-	50 µA Max.	-	$\overline{ST} = GND (SCG)$	
Duty		tw/ t	45 % to 55 % 50 % \		50 % VDD, $CL = Max$ .		
Output voltage		Vон	VDD -0.4 V Min.		2.2 V Min.	Iон = -8 mA	
Output load condition		Vol	0.4 V Max.		0.4 V Max.	IOL = 8  mA	
		Cl	25 pF		15 pF		
Output anable / diag	ble input veltege	Vih	0.7 VDD Min.		0.7 Vdd Min.	OE, ST	
Output enable / disable input voltage		VIL	0.2 Vpd Max.		0.3 Vdd Max.	OE, ST	
Output rise time		tR	4.0 ns Max.		7 ns Max.	$20 \% \rightarrow 80 \%$ VDD, CL $\leq$ Max.	
Output fall time		tF	4.0 ns Max.		7 ns Max.	$80 \% \rightarrow 20 \%$ VDD, CL $\leq$ Max.	
Oscillation start up time		tosc	12 ms Max.		10 ms Max.	Time at minimum operating voltage to be 0 s	
Aging		fa	±5 x 10 <sup>-6</sup> / year Max.			Ta = +25  °C, VDD = 3.3  V First year	
Shock resistance		S.R.	±20 x 10 <sup>-6</sup> Max.			Three drops on a hard board from 750 mm or excitation test with 29400 m/s² x 0.3 ms x 1/2sine wave in 3 directions	

### Specifications (characteristics)

			Specifications					
Item		Symbol	SG-615PTW / STW SG-531PTW / STW	SG-615PHW / SHW SG531PHW / SHW	SG-615PCW / SCW SG-531PCW / SCW	Remarks		
Nominal frequency range		fo	55.0001 MHz to 135.0000 MHz 26.0001 MHz to 13		26.0001 MHz to 135.0000 MHz	Refer to Operating condition and Frequency range		
Power source	Max. supply voltage	VDD-GND	-0.5 V to +7.0 V					
voltage	Operating voltage	Vdd	5.0 V =	$5.0 V \pm 0.5 V$ $3.3 V \pm 0.3 V$				
Temperature	Storage temperature	Tstg		-55 °C to +100 °C		Stored as bare product after unpacking		
range	Operating temperature	Topr		o +70 ℃	-40 °C to +85 °C	Refer to Operating condition and Frequency range		
Frequency stability		Δf/fo	B : ±50 x 10 <sup>-6</sup> C : ±100 x 1		) <sup>-6</sup>	-20 °C to +70 °C		
Frequency stability		Δ1/10	-		M : ±100 x 10 <sup>-6</sup>	-40 °C to +85 °C		
Current consumptio	n	ЮР	45 mA Max. 28 mA Max.		No load condition			
Output disable curre	ent	IOE	30 mA Max. 16 mA Max.		16 mA Max.	OE = GND (P*W)		
Standby current		lsт	50 µA Max.		$\overline{ST} = GND (S*W)$			
			40 % to 60 % 45 % to 55 %	-	-	TTL load : 1.4 V, CL = Max. TTL load : 1.4 V, 5TTL + 15 pF, fo $\leq$ 66.6667 MHz		
Duty		tw/ t	- - -	40 % to 60 % 45 % to 55% -	40 % to 60 % - 45 % to 55 %	CMOS load : 50% Vdd, CL = Max. CMOS load : 50% Vdd, CL = 25 pF, fo $\leq$ 66.6667 MHz CMOS load : 50% Vdd, CL = 25 pF, fo $\leq$ 40.0 MHz		
		Vон				Iон = -16 mA (*TW / *HW) / -8 mA (*CW)		
Output voltage		Vol		0.4 V Max.		IoL = 16 mA (*TW / *HW) / 8 mA (*CW)		
Output load condition			15 pF 5 TTL + 15 pF 25 pF			fo ≤ 135 MHz fo ≤ 90 MHz fo ≤ 66.6667 MHz		
		CL	- - - -	15 pF 25 pF 50 pF	15 pF -  30 pF	fo ≤ 135 MHz fo ≤ 125 MHz fo ≤ 66.6667MHz fo ≤ 40.0 MHz		
		Vih	2.0 V Min.		0.7 VDD Min.	OE, ST		
Output enable / disa	able input voltage	VIL	0.8 V Max.		0.2 Vdd Max.	0E, ST		
					2.0 ns Max. 4.0 ns Max.			TTL load: 0.8 V $\rightarrow$ 2.0 V, CL = Max. TTL load: 0.4 V $\rightarrow$ 2.4 V, CL = Max.
Output rise time		tR	- - -	3.0 ns Max. _ 4.0 ns Max.	_ 3.0 ns Max. 4.0 ns Max.	CMOS load: 80 % $\rightarrow$ 20 % VDD, CL = 25 pF CMOS load: 80 % $\rightarrow$ 20 % VDD, CL = 15 pF CMOS load: 80 % $\rightarrow$ 20 % VDD, CL = Max.		
Output fall time			2.0 ns Max. 4.0 ns Max.			TTL load: 2.0 V $\rightarrow$ 0.8 V, CL = Max. TTL load: 2.4 V $\rightarrow$ 0.4 V, CL = Max.		
		t⊧	- - -	3.0 ns Max. _ 4.0 ns Max.	_ 3.0 ns Max. 4.0 ns Max.	CMOS load: 80 % $\rightarrow$ 20 % VDD, CL = 25 pF CMOS load: 80 % $\rightarrow$ 20 % VDD, CL = 15 pF CMOS load: 80 % $\rightarrow$ 20 % VDD, CL = Max.		
Oscillation start up time		tosc	10 ms Max.			Time at minimum operating voltage to be 0 s		
Aging		fa	±5 x 10 <sup>-6</sup> / year Max.		Ta = +25 °C, VDD = 5.0 V / 3.3 V, First year			
Shock resistance		S.R.	±20 x 10 <sup>-6</sup> Max.		Three drops on a hard board from 750 mm or excitation test with 29400 m/s $^2$ x 0.3 ms x 1/2sine wave in 3 directions			

# THE CRYSTALMASTER



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EPSON offers effective savings to its customers through a wide range of electronic devices, such as semiconductors, liquid crystal display (LCD) modules, and crystal devices. These savings are achieved through a sophisticated melding of three different efficiency technologies.

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In 1988, Seiko Epson led in working to abolish CFCs, and perfect abolition of those ozone layer-destroying substances was achieved in 1992. In 1998, the 10th year of start of the CFC-free activity, Seiko Epson set this year as the "Second Environmental Benchmark Year" and established a new corporate General Environmental Policy. Seiko Epson is tackling with environmental issues comprehensively.

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To strengthen management for environmental activities, Seiko Epson Group aims at acquisition of the ISO14001 certification for Japanese and abroad main business bases (including affiliates) for manufacturing, sales, software development and others.

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Seiko-Epson quickly began working to acquire company-wide ISO9000 series certification, and has acquired ISO9001 or ISO9002 certification with all targeted products manufactured in Japanese and overseas plants.

The Quartz Device Operations Division (Ina Japan, EPM and SZE) have acquired QS-9000 certification, which are of higher level.

by blending the essence of these three efficiency technologies. The essence of these technologies is represented in each of the products that we provide to our customers.

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#### Co-existence Mark

The environmental mark symbolizing Epson's basic stance of "Co-existence with Nature". The design incorporates a fish, flower, and water, representing mutually supportive co-existence.

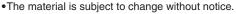


ISO14000 is an international standard for environmental management that was established by the International Standards Organization in 1996 against the background of growing concern regarding global warming, destruction of the ozone layer, and global deforestation.



#### QS-9000:

This is an enhanced standard for quality assurance systems formulated by leading U.S. automobile manufacturers based on the international ISO 9000 series.



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